2048 BIT ELECTRICALLY PROGRAMMABLE READ ONLY MEMORY

1602A–ELECTRICALLY PROGRAMMABLE
1702A–ERASABLE & ELECTRICALLY REPROGRAMMABLE

- **Fast Programming -- 2 minutes for all 2048 bits**
- **All 2048 bits guaranteed* programmable -- 100% factory tested**
- **Fully Decoded, 256x8 organization**
- **Static MOS -- No Clocks Required**
- **Inputs and Outputs DTL and TTL compatible**
- **Three-state Output -- OR-tie Capability**
- **Simple Memory Expansion -- Chip select input lead**

The 1602A and 1702A are 256 word by 8-bit electrically programmable ROMs ideally suited for uses where fast turn-around and pattern experimentation are important. The 1602A and 1702A undergo complete programming and functional testing on each bit position prior to shipment, thus insuring 100% programmability.

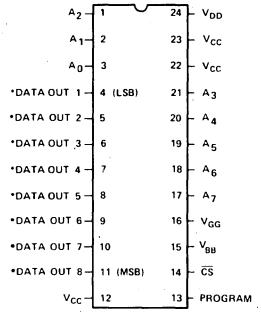
The 1602A and 1702A use identical chips. The 1702A is packaged in a 24 pin dual in-line package with a transparent lid. The transparent lid allows the user to expose the chip to ultraviolet light to erase the bit pattern. A new pattern can then be written into the device. The 1602A is packaged in a 24 pin dual in-line package with a metal lid and is not erasable.

The circuitry of the 1602A/1702A is entirely static; no clocks are required.

A pin-for-pin metal mask programmed ROM, the Intel 1302, is ideal for large volume production runs of systems initially using the 1602A or 1702A.

The 1602A/1702A is fabricated with silicon gate technology. This low threshold technology allows the design and production of higher performance MOS circuits and provides a higher functional density on a monolithic chip than conventional MOS technologies.

PIN CONFIGURATION



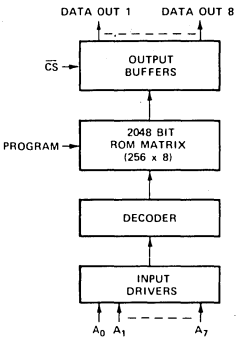
*THIS PIN IS THE DATA INPUT LEAD DURING PROGRAMMING

See page 3-8 for operational connection.

PIN NAMES

A_0–A_7	Address Inputs
$\overline{CS}$	Chip Select Input
D_{OUT1}–D_{OUT8}	Data Outputs

BLOCK DIAGRAM



NOTE: In the read mode a logic 1 at the address inputs and data outputs is a high and logic 0 is a low.

U.S. Patent No. 3660819

*Intel's liability shall be limited to replacing any unit which fails to program as desired.

PIN CONNECTIONS

The external lead connections to the 1602A/1702A differ, depending on whether the device is being programmed or used in read mode. (See following table.) In the programming mode, the data inputs 1-8 are pins 4-11 respectively.

PIN / MODE	12 (V_{CC})	13 (Program)	14 ($\overline{CS}$)	15 (V_{BB})	16 (V_{GG})	22 (V_{CC})	23 (V_{CC})
Read	V_{CC}	V_{CC}	GND	V_{CC}	V_{GG}	V_{CC}	V_{CC}
Programming	GND	Program Pulse	GND	V_{BB}	Pulsed V_{GG} (V_{IL4P})	GND	GND

Absolute Maximum Ratings *

Ambient Temperature Under Bias . . . . . 0°C to +70°C
Storage Temperature . . . . . −65°C to +125°C
Soldering Temperature of Leads (10 sec) . . . . . +300°C
Power Dissipation . . . . . 2 Watts
Read Operation: Input Voltages and Supply Voltages with respect to V_{CC} . . . . . +0.5V to −20V
Program Operation: Input Voltages and Supply Voltages with respect to V_{CC} . . . . . −48V

*COMMENT

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or at any other condition above those indicated in the operational sections of this specification is not implied. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability.

READ OPERATION

D.C. and Operating Characteristics

T_A = 0°C to 70°C, V_{CC} = +5V±5%, V_{DD} = −9V±5%, V_{GG} [1] = −9V±5%, unless otherwise noted. Typical values are at nominal voltages and T_A = 25°C.

SYMBOL	TEST	MIN.	TYP.	MAX.	UNIT	CONDITIONS
I_{LI}	Address and Chip Select Input Load Current			1	µA	V_{IN} = 0.0V
I_{LO}	Output Leakage Current			1	µA	V_{OUT} = 0.0V, $\overline{CS}$ = V_{CC} −2
I_{DDO}	Power Supply Current		5	10	mA	V_{GG}=V_{CC}, $\overline{CS}$=V_{CC}−2, I_{OL} = 0.0mA, T_A = 25°C — Note 1
I_{DD1}	Power Supply Current		35	50	mA	$\overline{CS}$=V_{CC} −2, I_{OL} =0.0mA, T_A = 25°C
I_{DD2}	Power Supply Current		32	46	mA	$\overline{CS}$=0.0, I_{OL} =0.0mA, T_A = 25°C
I_{DD3}	Power Supply Current		38.5	60	mA	$\overline{CS}$=V_{CC} −2, I_{OL} =0.0mA, T_A = 0°C
I_{CF1}	Output Clamp Current		8	14	mA	V_{OUT} = −1.0V, T_A = 0°C
I_{CF2}	Output Clamp Current			13	mA	V_{OUT} = −1.0V, T_A = 25°C
I_{GG}	Gate Supply Current			1	µA	
V_{IL1}	Input Low Voltage for TTL Interface	−1.0		0.65	V	
V_{IL2}	Input Low Voltage for MOS Interface	V_{DD}		V_{CC} −6	V	
V_{IH}	Address and Chip Select Input High Voltage	V_{CC} −2		V_{CC} +0.3	V	
I_{OL}	Output Sink Current	1.6	4		mA	V_{OUT} = 0.45V
I_{OH}	Output Source Current	−2.0			mA	V_{OUT} = 0.0V
V_{OL}	Output Low Voltage		−.7	0.45	V	I_{OL} = 1.6mA
V_{OH}	Output High Voltage	3.5	4.5		V	I_{OH} = −100 µA

NOTE 1: POWER-DOWN OPTION: V_{GG} may be clocked to reduce power dissipation. The average I_{DD} will vary between I_{DDO} and I_{DD1} depending on the V_{GG} duty cycle (see typical characteristics). For this option please specify 1702AL or 1602AL.

A.C. Characteristics

T_A = 0°C to +70°C, V_{CC} = +5V ±5%, V_{DD} = −9V ±5%, V_{GG} = −9V ±5% unless otherwise noted

SYMBOL	TEST	MINIMUM	TYPICAL	MAXIMUM	UNIT
Freq.	Repetition Rate			1	MHz
t_{OH}	Previous read data valid			100	ns
t_{ACC}	Address to output delay		0.7	1	µs
t_{DVGG}	Clocked V_{GG} set up (Note 1)	1			µs
t_{CS}	Chip select delay			100	ns
t_{CO}	Output delay from $\overline{CS}$			900	ns
t_{OD}	Output deselect			300	ns
t_{OHC}	Data out hold in clocked V_{GG} mode (Note 1)			5	µs

Capacitance* T_A = 25°C

SYMBOL	TEST	MINIMUM	TYPICAL	MAXIMUM	UNIT	CONDITIONS
C_{IN}	Input Capacitance		8	15	pF	$V_{IN} = V_{CC}$, $\overline{CS} = V_{CC}$, $V_{OUT} = V_{CC}$, $V_{GG} = V_{CC}$ — All unused pins are at A.C. ground
C_{OUT}	Output Capacitance		10	15	pF	
$C_{V_{GG}}$	V_{GG} Capacitance (Note 1)			30	pF	

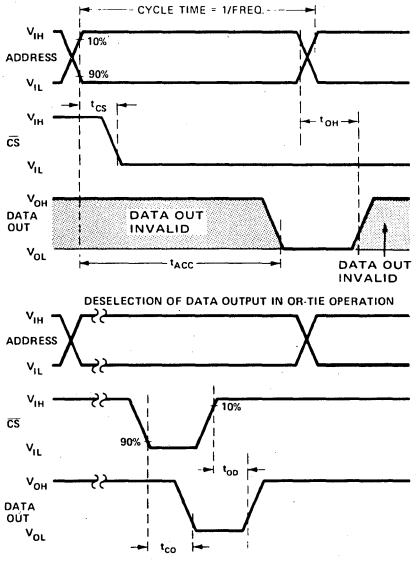
*This parameter is periodically sampled and is not 100% tested.

Switching Characteristics

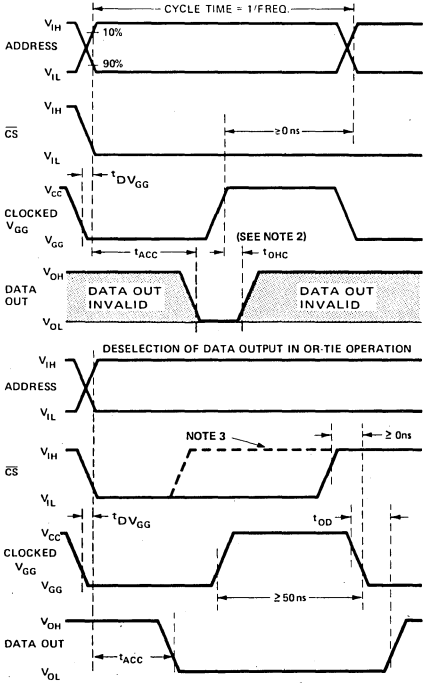
Conditions of Test:

Input pulse amplitudes: 0 to 4V; t_R, t_F ≤50 ns
Output load is 1 TTL gate; measurements made at output of TTL gate (t_{PD}≤15 ns), C_L=15pF

A) Constant V_{GG} Operation



B) Power-Down Option (See Note 1)

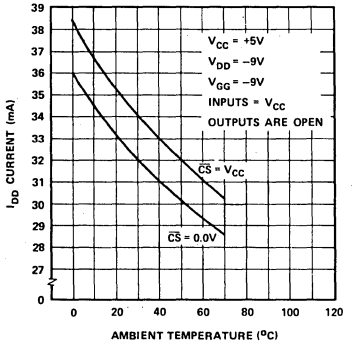


NOTE 2: The output will remain valid for t_{OHC} as long as clocked V_{GG} is at V_{CC}. An address change may occur as soon as the output is sensed (clocked V_{GG} may still be at V_{CC}). Data becomes invalid for the old address when clocked V_{GG} is returned to V_{GG}.

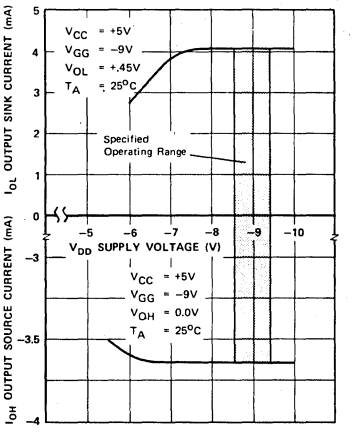
NOTE 3: If $\overline{CS}$ makes a transition from V_{IL} to V_{IH} while clocked V_{GG} is at V_{GG}, then deselection of output occurs at t_{OD} as shown in static operation with constant V_{GG}.

Typical Characteristics

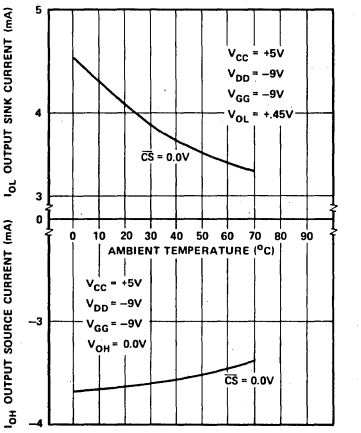
I_{DD} CURRENT VS. TEMPERATURE



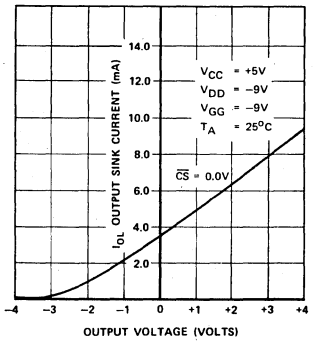
OUTPUT CURRENT VS. V_{DD} SUPPLY VOLTAGE



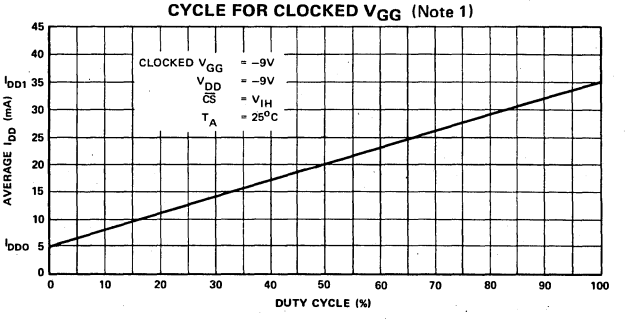
OUTPUT CURRENT VS. TEMPERATURE



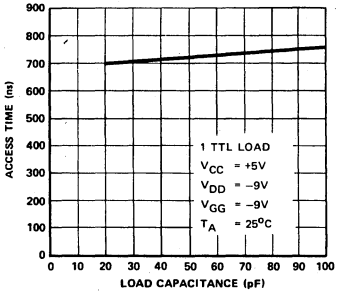
OUTPUT SINK CURRENT VS. OUTPUT VOLTAGE



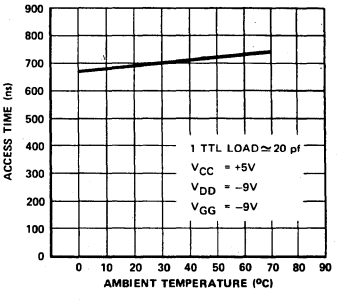
AVERAGE CURRENT VS. DUTY CYCLE FOR CLOCKED V_{GG} (Note 1)



ACCESS TIME VS. LOAD CAPACITANCE



ACCESS TIME VS. TEMPERATURE



PROGRAMMING OPERATION

D.C. and Operating Characteristics for Programming Operation

$T_A = 25°C$, $V_{CC} = 0V$, $V_{BB} = +12V \pm 10\%$, $\overline{CS} = 0V$ unless otherwise noted

SYMBOL	TEST	MIN.	TYP.	MAX.	UNIT	CONDITIONS
I_{LI1P}	Address and Data Input Load Current			10	mA	$V_{IN} = -48V$
I_{LI2P}	Program and V_{GG} Load Current			10	mA	$V_{IN} = -48V$
I_{BB}	V_{BB} Supply Load Current		10		mA	(Note 5)
I_{DDP}	Peak I_{DD} Supply Load Current		200		mA	$V_{DD} = V_{prog} = -48V$ $V_{GG} = -35V$ (Note 4)
V_{IHP}	Input High Voltage			0.3	V	
V_{IL1P}	Pulsed Data Input Low Voltage	−46		−48	V	
V_{IL2P}	Address Input Low Voltage	−40		−48	V	
V_{IL3P}	Pulsed Input Low V_{DD} and Program Voltage	−46		−48	V	
V_{IL4P}	Pulsed Input Low V_{GG} Voltage	−35		−40	V	

Note 4: I_{DDP} flows only during V_{DD}, V_{GG} on time. I_{DDP} should not be allowed to exceed 300mA for greater than 100μsec. Average power supply current I_{DDP} is typically 40mA at 20% duty cycle.

Note 5: The V_{BB} supply must be limited to 100mA max. current to prevent damage to the device.

A.C. Characteristics for Programming Operation

$T_{AMBIENT} = 25°C$, $V_{CC} = 0V$, $V_{BB} = +12V \pm 10\%$, $\overline{CS} = 0V$ unless otherwise noted

SYMBOL	TEST	MIN.	TYP.	MAX.	UNIT	CONDITIONS
	Duty Cycle (V_{DD}, V_{GG})			20	%	
$t_{\phi PW}$	Program Pulse Width			3	ms	$V_{GG} = -35V$, $V_{DD} = V_{prog} = -48V$
t_{DW}	Data Set Up Time	25			μs	
t_{DH}	Data Hold Time	10			μs	
t_{VW}	V_{DD}, V_{GG} Set Up	100			μs	
t_{VD}	V_{DD}, V_{GG} Hold	10		100	μs	
t_{ACW} (6)	Address Complement Set Up	25			μs	
t_{ACH} (6)	Address Complement Hold	25			μs	
t_{ATW}	Address True Set Up	10			μs	
t_{ATH}	Address True Hold	10			μs	

Note 6: All 8 address bits must be in the complement state when pulsed V_{DD} and V_{GG} move to their negative levels. The addresses (0 through 255) must be programmed as shown in the timing diagram for a minimum of 32 times.

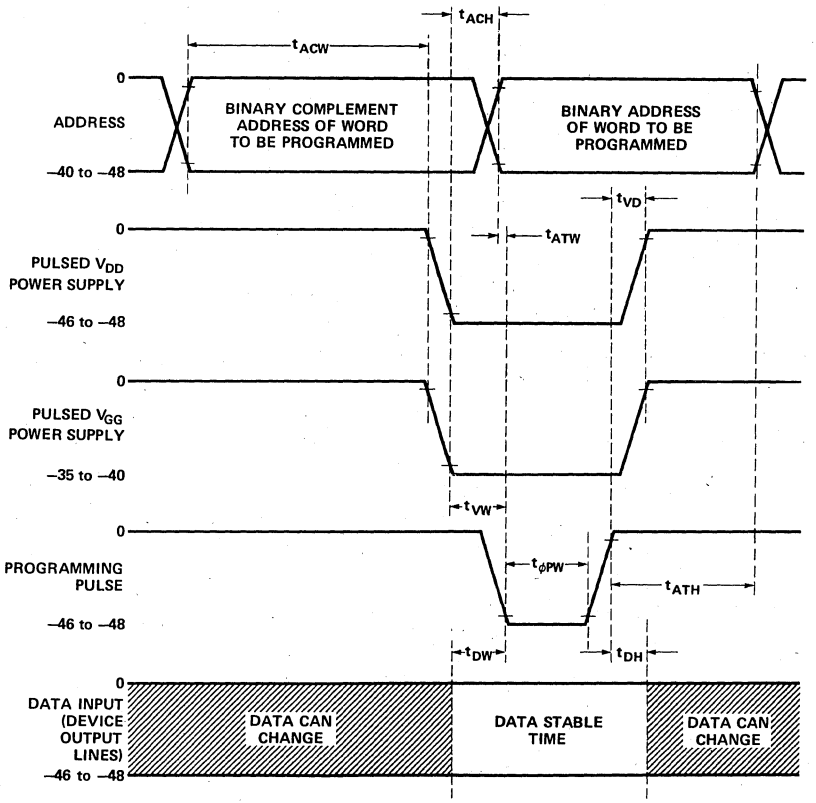
Switching Characteristics for Programming Operation

Conditions of Test:

Input pulse rise and fall times $\leq 1\mu$sec

$\overline{CS}$ = 0V

PROGRAM WAVEFORMS



OPERATION OF THE 1602A/1702A IN PROGRAM MODE

Initially, all 2048 bits of the ROM are in the "0" state (output low). Information is introduced by selectively programming "1"s (output high) in the proper bit locations.

Word address selection is done by the same decoding circuitry used in the READ mode (see table on page 3-11 for logic levels). All 8 address bits must be in the binary complement state when pulsed V_{DD} and V_{GG} move to their negative levels. The addresses must be held in their binary complement state for a minimum of 25μsec after V_{DD} and V_{GG} have moved to their negative levels. The addresses must then make the transition to their true state a minimum of 10μsec before the program pulse is applied. The addresses should be programmed in the sequence 0 through 255 for a minimum of 32 times. The eight output terminals are used as data inputs to determine the information pattern in the eight bits of each word. A low data input level (-48V) will program a "1" and a high data input level (ground) will leave a "0" (see table on page 3-11). All eight bits of one word are programmed simultaneously by setting the desired bit information patterns on the data input terminals.

During the programming, V_{GG}, V_{DD} and the Program Pulse are pulsed signals.

1702A ERASING PROCEDURE

The 1702A may be erased by exposure to high intensity short-wave ultraviolet light at a wavelength of 2537Å. The recommended integrated dose (i.e., UV intensity x exposure time) is 6W-sec/cm^2. Examples of ultraviolet sources which can erase the 1702A in 10 to 20 minutes are the Model UVS-54 and Model S-52 short-wave ultraviolet lamps manufactured by Ultra-Violet Products, Inc. (5114 Walnut Grove Avenue, San Gabriel, California). The lamps should be used without short-wave filters, and the 1702A to be erased should be placed about one inch away from the lamp tubes.

2048 BIT ELECTRICALLY PROGRAMMABLE READ ONLY MEMORY

1602A-6 ELECTRICALLY PROGRAMMABLE
1702A-6 ERASABLE & ELECTRICALLY REPROGRAMMABLE

- **Fast Programming -- 2 minutes for all 2048 bits**
- **All 2048 bits guaranteed* programmable -- 100% factory tested**
- **Fully Decoded, 256x8 organization**
- **Static MOS -- No Clocks Required**
- **Inputs and Outputs DTL and TTL compatible**
- **Three-state Output -- OR-tie Capability**
- **Simple Memory Expansion -- Chip select input lead**
- **1.5 µs Access Time**

The 1602A-6 and 1702A-6 are 256 word by 8-bit electrically programmable ROMs ideally suited for uses where fast turn-around and pattern experimentation are important. The 1602A-6 and 1702A-6 undergo complete programming and functional testing on each bit position prior to shipment thus insuring 100% programmability.

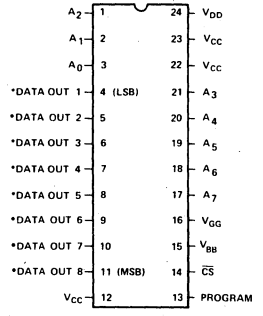
The 1602A-6 and 1702A-6 use identical chips. The 1702A-6 is packaged in a 24 pin dual in-line package with a transparent lid. The transparent lid allows the user to expose the chip to ultraviolet light to erase the bit pattern. A new pattern can then be written into the device. The 1602A-6 is packaged in a 24 pin dual in-line package with a metal lid and is not erasable.

The circuitry of the 1602A-6 and 1702A-6 is entirely static; no clocks are required.

A pin-for-pin metal mask programmed ROM, the Intel 1302, is ideal for large volume production runs of systems initially using the -6 devices.

The 1602A-6 and 1702A-6 are fabricated with silicon gate technology. This low threshold technology allows the design and production of higher performance MOS circuits and provides a higher functional density on a monolithic chip than conventional MOS technologies.

PIN CONFIGURATION



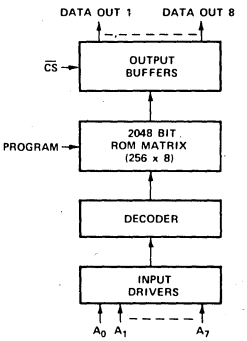
*THIS PIN IS THE DATA INPUT LEAD DURING PROGRAMMING

See page 3-15 for operational connection.

PIN NAMES

A_0–A_7	Address Inputs
$\overline{CS}$	Chip Select Input
D_{OUT1}–D_{OUT8}	Data Outputs

BLOCK DIAGRAM



NOTE: In the read mode a logic 1 at the address inputs and data outputs is a high and logic 0 is a low.

*Intel's liability shall be limited to replacing any unit which fails to program as desired.

U.S. Patent No. 3660819

PIN CONNECTIONS

The external lead connections to the 1602A-6/1702A-6 differ, depending on whether the device is being programmed or used in the read mode. (See following table.) In the programming mode, the data inputs 1-8 are pins 4-11 respectively.

MODE \ PIN	12 (V_{CC})	13 (Program)	14 ($\overline{CS}$)	15 (V_{BB})	16 (V_{GG})	22 (V_{CC})	23 (V_{CC})
Read	V_{CC}	V_{CC}	GND	V_{CC}	V_{GG}	V_{CC}	V_{CC}
Programming	GND	Program Pulse	GND	V_{BB}	Pulsed V_{GG} (V_{IL4P})	GND	GND

Absolute Maximum Ratings*

Ambient Temperature Under Bias . . . . . 0°C to +70°C
Storage Temperature . . . . . −65°C to +125°C
Soldering Temperature of Leads (10 sec) . . . . . +300°C
Power Dissipation . . . . . 2 Watts
Read Operation: Input Voltages and Supply Voltages with respect to V_{CC} . . . . . +0.5V to −20V
Program Operation: Input Voltages and Supply Voltages with respect to V_{CC} . . . . . −48V

*COMMENT

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or at any other condition above those indicated in the operational sections of this specification is not implied. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability.

READ OPERATION

D.C. and Operating Characteristics

T_A = 0°C to 70°C, V_{CC} = +5V±5%, V_{DD} = −9V±5%, V_{GG} [1] = −9V±5%, unless otherwise noted. Typical values are at nominal voltages and T_A = 25°C.

SYMBOL	TEST	MIN.	TYP.	MAX.	UNIT	CONDITIONS
I_{LI}	Address and Chip Select Input Load Current			1	µA	V_{IN} = 0.0V
I_{LO}	Output Leakage Current			1	µA	V_{OUT} = 0.0V, $\overline{CS}$ = V_{CC} −2
I_{DDO}	Power Supply Current		5	10	mA	V_{GG}=V_{CC}, $\overline{CS}$=V_{CC}−2, I_{OL} = 0.0mA, T_A = 25°C — Note 1
I_{DD1}	Power Supply Current		35	50	mA	$\overline{CS}$=V_{CC} −2, I_{OL} =0.0mA, T_A = 25°C
I_{DD2}	Power Supply Current		32	46	mA	$\overline{CS}$=0.0, I_{OL} =0.0mA, T_A = 25°C
I_{DD3}	Power Supply Current		38.5	60	mA	$\overline{CS}$=V_{CC} −2, I_{OL} =0.0mA , T_A = 0°C
I_{CF1}	Output Clamp Current		8	14	mA	V_{OUT} = −1.0V, T_A = 0°C
I_{CF2}	Output Clamp Current			13	mA	V_{OUT} = −1.0V, T_A = 25°C
I_{GG}	Gate Supply Current			1	µA	
V_{IL1}	Input Low Voltage for TTL Interface	−1.0		0.65	V	
V_{IL2}	Input Low Voltage for MOS Interface	V_{DD}		V_{CC} −6	V	
V_{IH}	Address and Chip Select Input High Voltage	V_{CC} −2		V_{CC} +0.3	V	
I_{OL}	Output Sink Current	1.6	4		mA	V_{OUT} = 0.45V
I_{OH}	Output Source Current	−2.0			mA	V_{OUT} = 0.0V
V_{OL}	Output Low Voltage		−.7	0.45	V	I_{OL} = 1.6mA
V_{OH}	Output High Voltage	3.5	4.5		V	I_{OH} = −100 µA

NOTE 1: POWER DOWN OPTION: V_{GG} may be clocked to reduce power dissipation. The average I_{DD} will vary between I_{DD0} and I_{DD1} depending on the V_{GG} duty cycle (see typical characteristics). For this option please specify 1602AL-6 or 1702AL-6.

A.C. Characteristics

T_A = 0° C to +70°C, V_{CC} = +5V ±5%, V_{DD} = −9V ±5%, V_{GG} = −9V ±5% unless otherwise noted

SYMBOL	TEST	MINIMUM	TYPICAL	MAXIMUM	UNIT
Freq.	Repetition Rate			0.66	MHz
t_{OH}	Previous read data valid			100	ns
t_{ACC}	Address to output delay		0.7	1.5	µs
t_{DVGG}	Clocked V_{GG} set up (Note 1)	1			µs
t_{CS}	Chip select delay			600	ns
t_{CO}	Output delay from $\overline{CS}$			900	ns
t_{OD}	Output deselect			300	ns
t_{OHC}	Data out hold in clocked V_{GG} mode (Note 1)			5	µs

Capacitance* T_A = 25°C

SYMBOL	TEST	MINIMUM	TYPICAL	MAXIMUM	UNIT	CONDITIONS
C_{IN}	Input Capacitance		8	15	pF	$V_{IN} = V_{CC}$, $\overline{CS} = V_{CC}$, $V_{OUT} = V_{CC}$, $V_{GG} = V_{CC}$ — All unused pins are at A.C. ground
C_{OUT}	Output Capacitance		10	15	pF	
$C_{V_{GG}}$	V_{GG} Capacitance (Note 1)			30	pF	

*This parameter is periodically sampled and is not 100% tested.

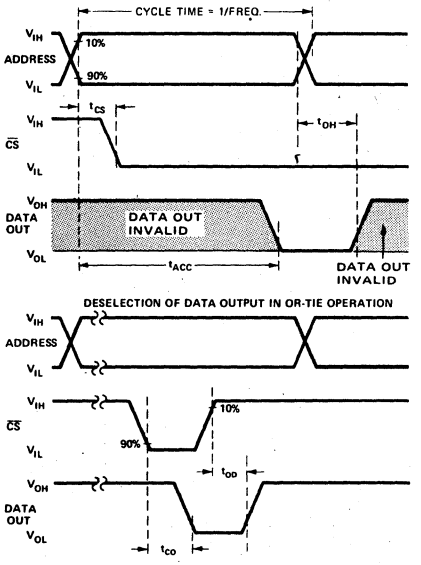
Switching Characteristics

Conditions of Test:

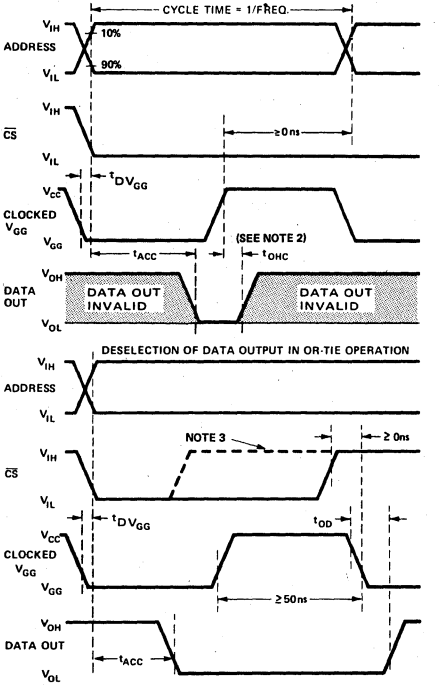
Input pulse amplitudes: 0 to 4V; t_R, t_F ≤50 ns

Output load is 1 TTL gate; measurements made at output of TTL gate (t_{PD}≤15 ns), C_L=15pF

A) Constant V_{GG} Operation



B) Power-Down Option (See Note 1)



NOTE 2: The output will remain valid for t_{OHC} as long as clocked V_{GG} is at V_{CC}. An address change may occur as soon as the output is sensed (clocked V_{GG} may still be at V_{CC}). Data becomes invalid for the old address when clocked V_{GG} is returned to V_{GG}.

NOTE 3: If $\overline{CS}$ makes a transition from V_{IL} to V_{IH} while clocked V_{GG} is at V_{GG}, then deselection of output occurs at t_{OD} as shown in static operation with constant V_{GG}.

All programming operation and erasing characteristics as described on pages 3-11 through 3-13 apply for the 1602A-6/1702A-6.